

Top View

www.vishay.com

Vishay Siliconix

Automotive N-Channel 100 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	100				
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.025				
$R_{DS(on)}$ (Ω) at $V_{GS} = 4.5 \text{ V}$	0.029				
I _D (A)	40				
Configuration	Single				
Package	TO-252 Reverse Lead DPAK				

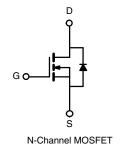
FEATURES

- TrenchFET® power MOSFET
- Package with low thermal resistance
- 100 % R_q and UIS tested
- AEC-Q101 qualified
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>





Bottom View



ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V _{DS}	100	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Current	T _C = 25 °C a	- I _D	40		
	T _C = 125 °C		26		
Continuous Source Current (Diode Conduction) a		I _S	40	Α	
Pulsed Drain Current ^b		I _{DM}	160		
Single Pulse Avalanche Current	L = 0.1 mH	I _{AS}	40		
Single Pulse Avalanche Energy	L = 0.1 IIIII	E _{AS}	80	mJ	
Maximum Power Dissipation ^b	T _C = 25 °C	D	136	W	
	T _C = 125 °C	P_{D}	45] vv	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to +175	°C	

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient PC	CB Mount c	R_{thJA}	50	°C/W	
Junction-to-Case (Drain)		R_{thJC}	1.1	C/VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width $\leq 300~\mu s,~duty~cycle \leq 2~\%.$
- c. When mounted on 1" square PCB (FR4 material).



www.vishay.com

Vishay Siliconix

PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT
Static		•					
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		100	-	-	V
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	$V_{DS} = V_{GS}, I_D = 250 \mu\text{A}$		-	2.5	V
Gate-Source Leakage	I _{GSS}	V _{DS} =	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$		-	± 100	nA
		$V_{GS} = 0 V$	V _{DS} = 100 V	-	-	1	μА
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 100 V, T _J = 125 °C	-	-	50	
		V _{GS} = 0 V	V _{DS} = 100 V, T _J = 175 °C	-	-	250	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	$V_{DS} \ge 5 \text{ V}$	50	-	-	Α
		V _{GS} = 10 V	I _D = 40 A	-	0.019	0.025	Ω
Drain-Source On-State Resistance a	Ь	V _{GS} = 10 V	I _D = 40 A, T _J = 125 °C	-	-	0.050	
Drain-Source On-State Resistance 4	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.063	
		V _{GS} = 4.5 V	I _D = 20 A	-	0.021	0.029	
Forward Transconductance b	9 _{fs}	V _{DS} = 15 V, I _D = 40 A		-	73	=.	S
Dynamic ^b							
Input Capacitance	C _{iss}			-	2703	3380	
Output Capacitance	Coss	$V_{GS} = 0 V$	$V_{DS} = 25 \text{ V}, f = 1 \text{ MHz}$	-	312	390	pF
Reverse Transfer Capacitance	C _{rss}			-	127	160	
Total Gate Charge ^c	Qg			-	46	70	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 50 \text{ V}, I_D = 40 \text{ A}$	-	8.2	-	nC
Gate-Drain Charge ^c	Q_{gd}			-	13	-	
Gate Resistance	R_g	f = 1 MHz		0.9	1.8	3.1	Ω
Turn-On Delay Time ^c	t _{d(on)}	$V_{DD} = 50 \text{ V}, \text{ R}_L = 1.25 \Omega$ $I_D \cong 40 \text{ A}, \text{ V}_{GEN} = 10 \text{ V}, \text{ R}_g = 1 \Omega$		-	11	17	
Rise Time ^c	t _r			-	11	17	ns
Turn-Off Delay Time ^c	t _{d(off)}			-	27	41	
Fall Time ^c	t _f			-	6	9	
Source-Drain Diode Ratings and Chara	acteristics ^b						
Pulsed Current ^a	I _{SM}			-	-	160	Α
Forward Voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.9	1.5	V

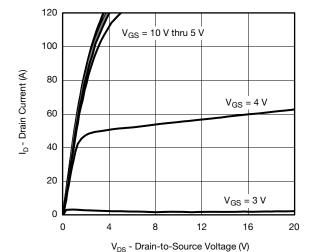
Notes

- a. Pulse test; pulse width $\leq 300~\mu s,$ duty cycle $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

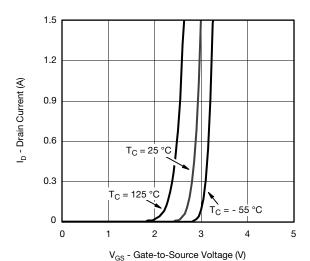
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



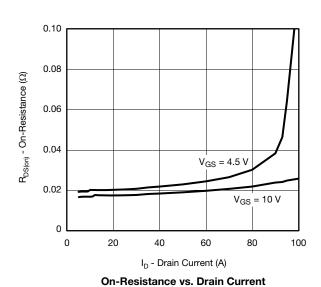
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



Output Characteristics

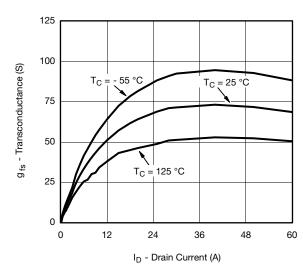


Transfer Characteristics

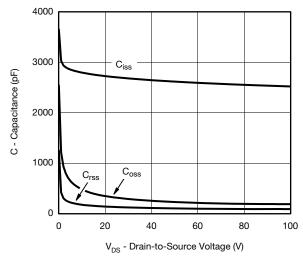


 $C_{C} = 125 \, ^{\circ}C$ $C_{C} = 125 \, ^{\circ}C$ $C_{C} = -55 \, ^{\circ}C$

Transfer Characteristics

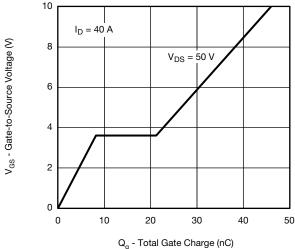


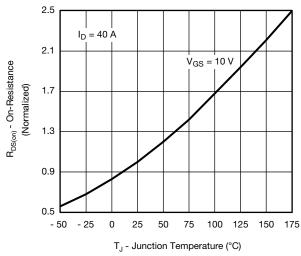
Transconductance





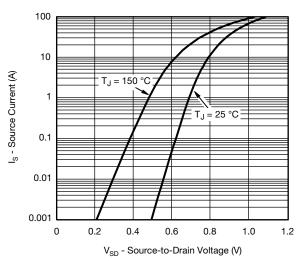
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)

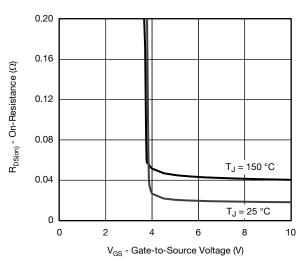




Gate Charge

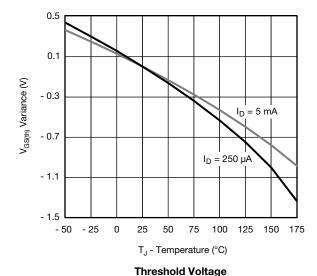


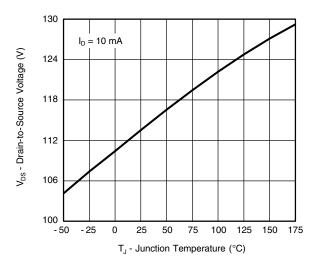




Source Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

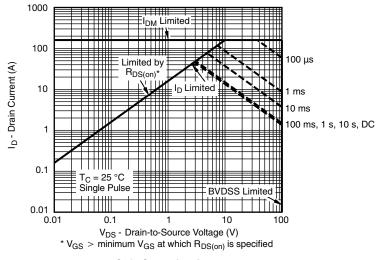




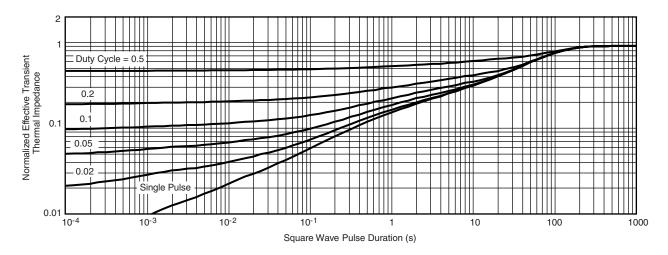
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



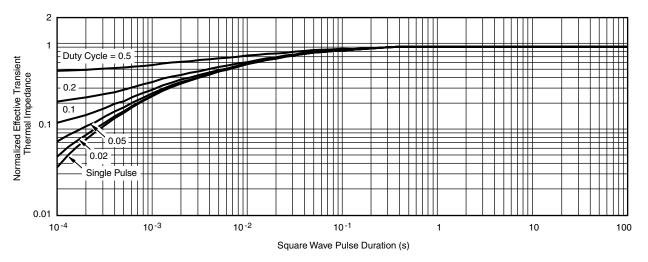
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C) are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg269060.



www.vishay.com

Vishay Siliconix

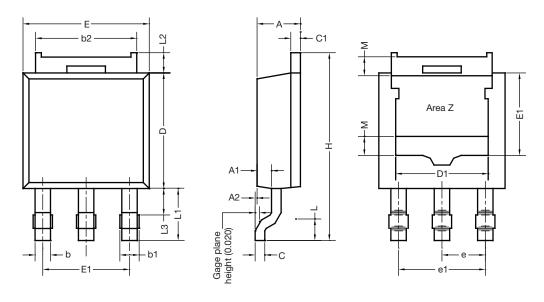
REVISION HISTORY ^a				
REVISION	DATE	DESCRIPTION OF CHANGE		
F	04-Aug-15	Revised R _g minimum limit		

Note

a. As of April 2014

Vishay Siliconix

TO-252 Reverse Lead Case Outline



Notes

- Dimension L3 for reference only
- Area Z: unplated area more than 80 % heatsink area and for partial plating part only

DIM.	MILL	IMETERS	INCHES			
	MIN.	MAX.	MIN.	MAX.		
A	2.23	2.33	0.088	0.092		
A1	0.64	0.89	0.025	0.035		
A2	0.03	0.18	0.001	0.007		
b	0.71	0.88	0.028	0.035		
b1	0.76	1.14	0.030	0.045		
b2	5.23	5.44	0.206	0.214		
С	0.46	0.58	0.018	0.023		
C1	0.46	0.58	0.018	0.023		
D	5.97	6.22	0.235	0.245		
D1	4.49	5.00	0.177	0.197		
E	6.48	6.73	0.255	0.265		
E1	4.32	-	0.170	-		
е	2.5	2.28 BSC		0.090 BSC		
e1	4.	4.57 BSC		0 BSC		
Н	9.65	10.41	0.380	0.410		
L	1.40	1.78	0.055	0.070		
L1	2.74 BSC		0.108 BSC			
L2	0.89	1.27	0.035	0.050		
L3	1.15	1.52	0.040	0.060		
М	-	1.00 (reference only)	-	0.039 (reference only)		

ECN: T16-0952-Rev. D, 16-Jan-17

DWG: 5894



Legal Disclaimer Notice

Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and / or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Hyperlinks included in this datasheet may direct users to third-party websites. These links are provided as a convenience and for informational purposes only. Inclusion of these hyperlinks does not constitute an endorsement or an approval by Vishay of any of the products, services or opinions of the corporation, organization or individual associated with the third-party website. Vishay disclaims any and all liability and bears no responsibility for the accuracy, legality or content of the third-party website or for that of subsequent links.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.